

DUAL N-CANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ C$
30V	3Ω @ $V_{GS} = 4.5V$	350 mA
	7Ω @ $V_{GS} = 2.5V$	

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.


Applications

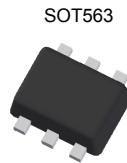
- Motor Control
- Power Management Functions
- DC-DC Converters
- Backlighting

Features and Benefits

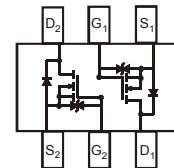
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (approximate)



Top View



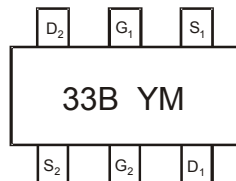
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN33D8LV-7	SOT563	3K/Tape & Reel
DMN33D8LV-13	SOT563	10K/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



33B = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: V = 2008
 M = Month ex: 9 = September

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	I_D	350	mA
Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$		200	
Maximum Continuous Body Diode Forward Current (Note 5)	I_S	0.5	A
Pulsed Drain Current (10 μs pulse, duty cycle=1%)	I_{DM}	0.8	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	0.43
		$T_A = +70^\circ\text{C}$	0.20
Thermal Resistance, Junction to Ambient (Note 5)	Steady State $R_{\theta JA}$	288	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	@ $T_C = +25^\circ\text{C}$ $V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	—	1.5	V	$V_{DS} = 3\text{V}, I_D = 100\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	2.4	Ω	$V_{GS} = 10\text{V}, I_D = 250\text{mA}$
		—	—	3.0		$V_{GS} = 4.5\text{V}, I_D = 250\text{mA}$
		—	—	5.0		$V_{GS} = 4.0\text{V}, I_D = 10\text{mA}$
		—	—	7.0		$V_{GS} = 2.5\text{V}, I_D = 10\text{mA}$
		—	—	—		—
Forward Transfer Admittance	$ Y_{fs} $	10	—	—	mS	$V_{DS} = 3\text{V}, I_D = 10\text{mA}$
Diode Forward Voltage	V_{SD}	—	—	1.2	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	48	—	pF	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V},$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	11	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	8	—	pF	
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	0.55	—	nC	$V_{GS} = 10\text{V}, V_{DS} = 10\text{V},$ $I_D = 250\text{mA}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	1.23	—	nC	
Gate-Source Charge	Q_{gs}	—	0.14	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.14	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	2.9	—	ns	
Turn-On Rise Time	t_r	—	2.6	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V},$ $R_G = 25\Omega, I_D = 200\text{mA}$
Turn-Off Delay Time	$t_{D(off)}$	—	18.2	—	ns	
Turn-Off Fall Time	t_f	—	13.6	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

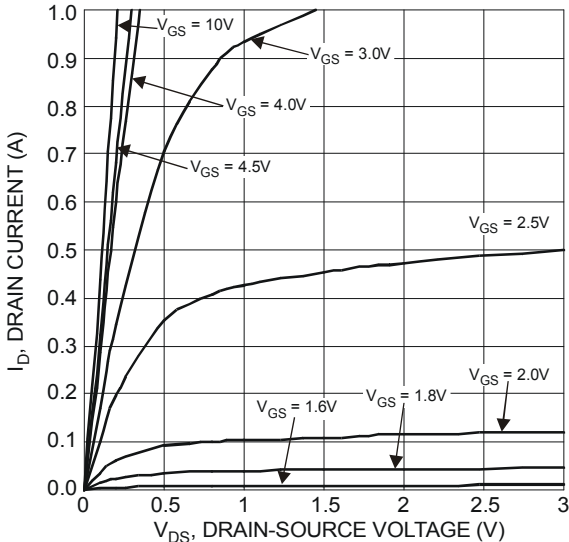


Figure 1 Typical Output Characteristics

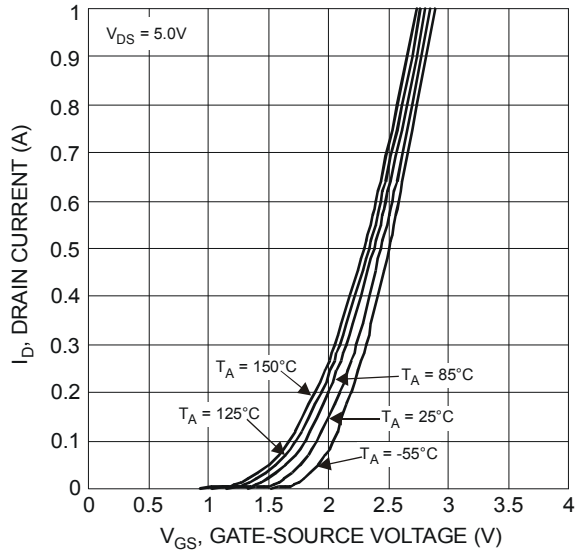


Figure 2 Typical Transfer Characteristics

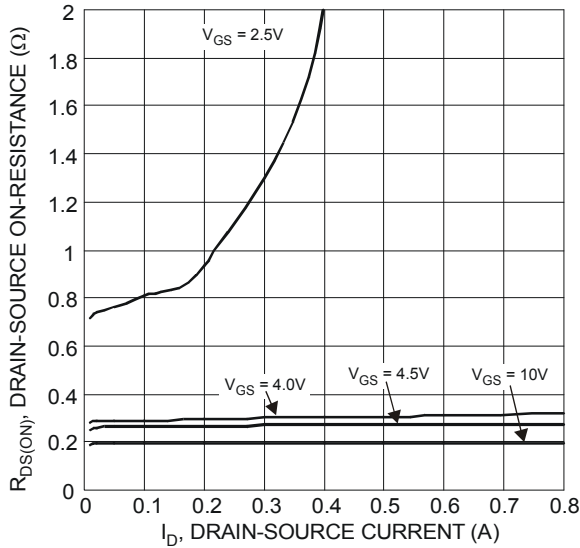


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

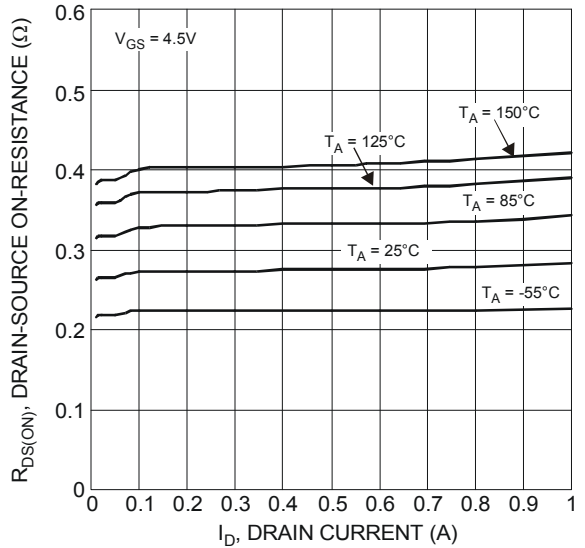


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

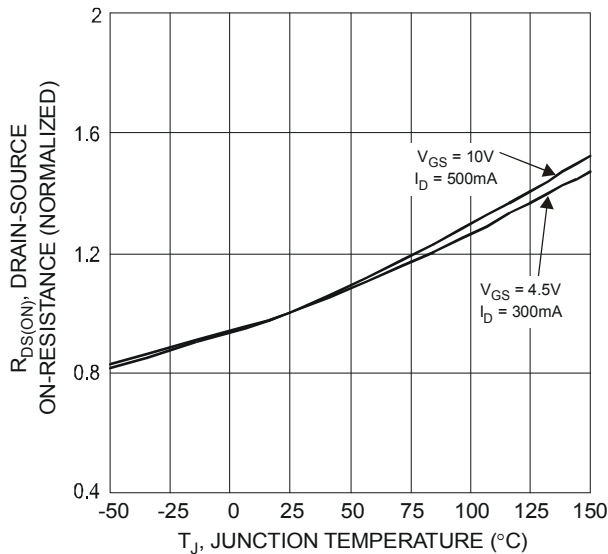


Figure 5 On-Resistance Variation with Temperature

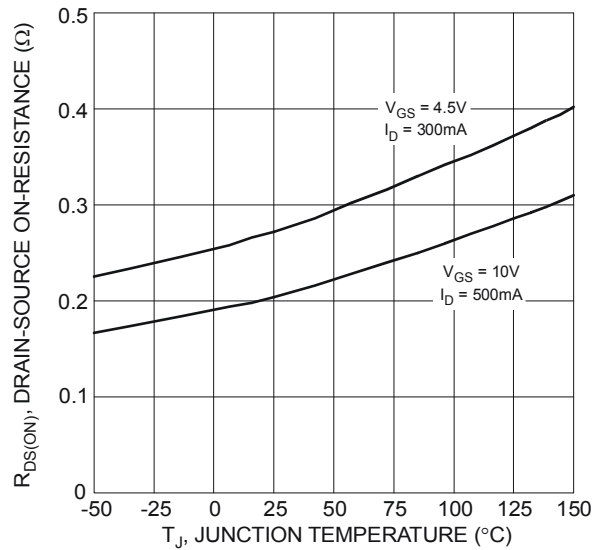


Figure 6 On-Resistance Variation with Temperature

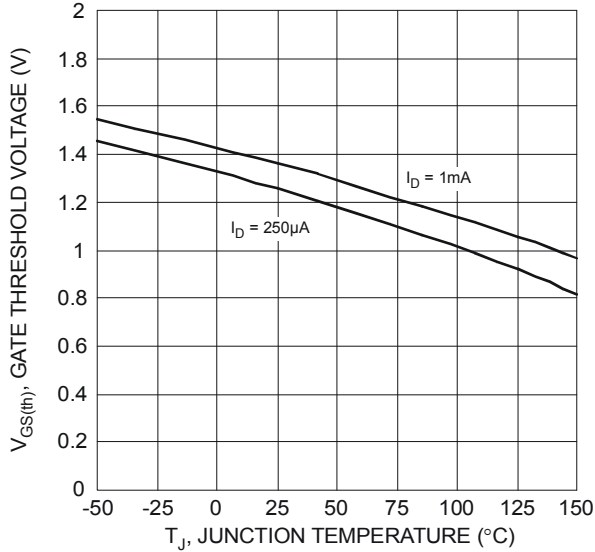


Figure 7 Gate Threshold Variation vs. Ambient Temperature

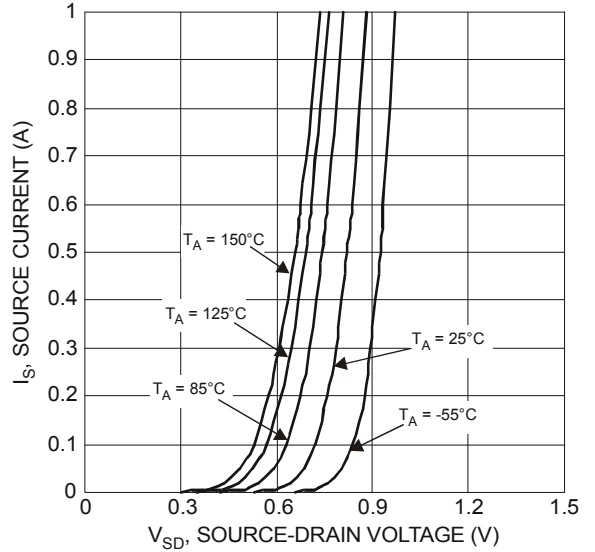


Figure 8 Diode Forward Voltage vs. Current

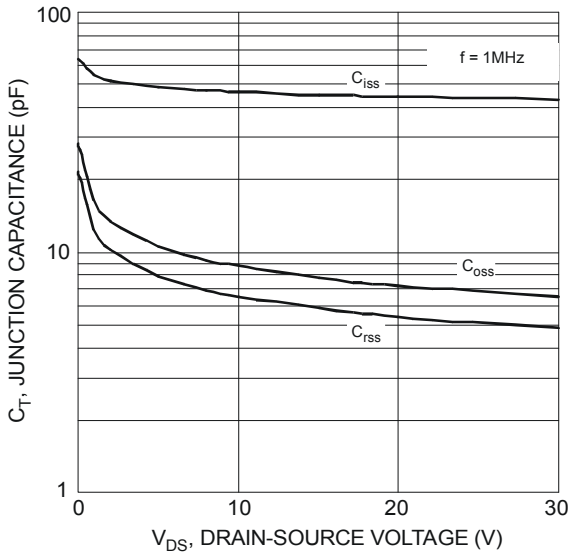


Figure 9 Typical Junction Capacitance

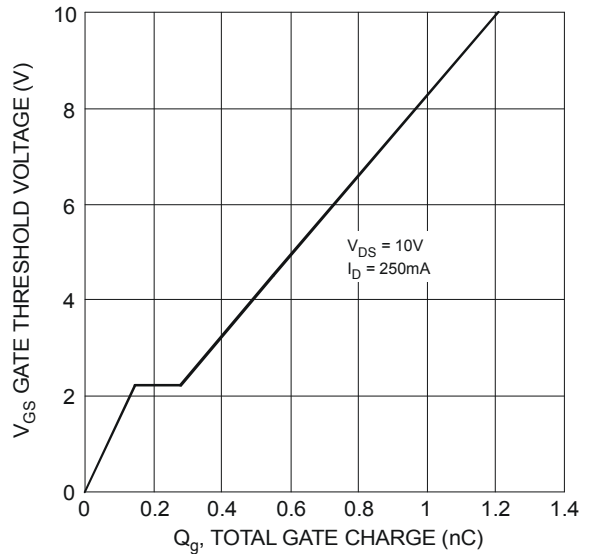


Figure 10 Gate Charge

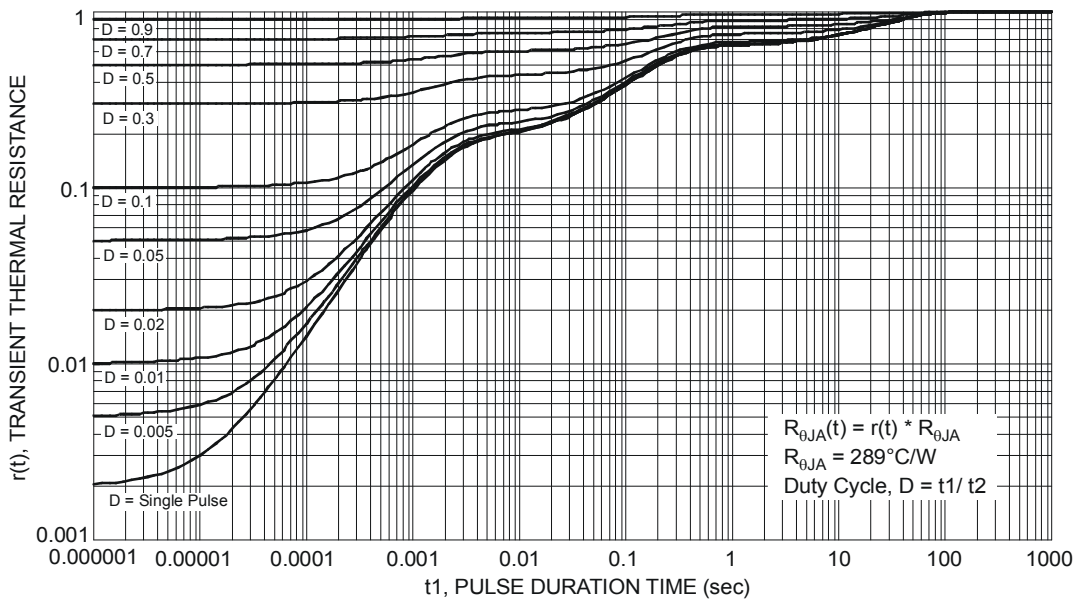
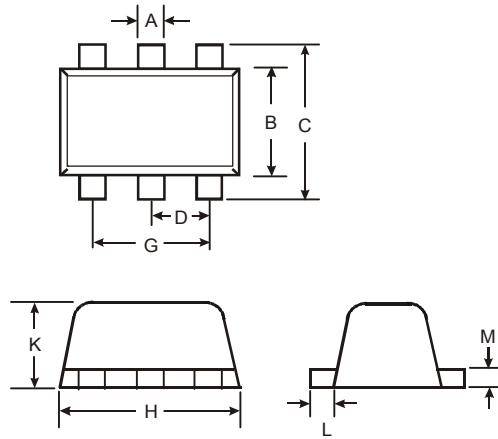


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

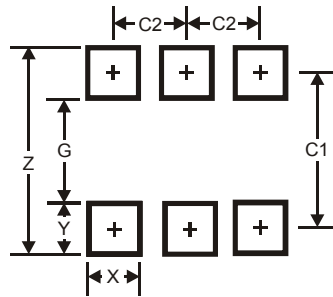
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

NEW PRODUCT

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